

Zhongda Li

List of Publications by Year in descending order

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22
papers

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1305906

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docs citations

22
times ranked

418
citing authors

#	ARTICLE	IF	CITATIONS
1	Sidewall Dominated Characteristics on Fin-Gate AlGaIn/GaN MOS-Channel-HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 3025-3031.	1.6	55
2	Design and Simulation of 5â€“20-kV GaN Enhancement-Mode Vertical Superjunction HEMT. IEEE Transactions on Electron Devices, 2013, 60, 3230-3237.	1.6	61
3	Robustness of GaN vertical superjunction HEMT. , 2013, , .		0
4	Metalâ€“Oxideâ€“Semiconductor Interface and Dielectric Properties of Atomic Layer Deposited SiO ₂ on GaN. Japanese Journal of Applied Physics, 2013, 52, 08JN24.	0.8	22
5	Design and Simulation of Novel Enhancement Mode 5â€“20 kV GaN Vertical Superjunction High Electron Mobility Transistors for Smart Grid Applications. Japanese Journal of Applied Physics, 2013, 52, 08JN01.	0.8	4
6	A New Method to Modify Two-Dimensional Electron Gas Density by GaN Cap Etching. Japanese Journal of Applied Physics, 2013, 52, 08JN11.	0.8	1
7	Avalanche Breakdown Design Parameters in GaN. Japanese Journal of Applied Physics, 2013, 52, 08JN05.	0.8	8
8	DC breakdown and TDDDB study of ALD SiO ₂ on GaN. , 2012, , .		1
9	High voltage normally-off GaN MOSC-HEMTs on silicon substrates for power switching applications. , 2012, , .		11
10	Isolation methods for GaN lateral MOS-channel HEMTs. , 2012, , .		0
11	Design of GaN and SiC 5â€“20kV vertical superjunction structures. , 2012, , .		2
12	Study of CF ₄ plasma treatment in drift region optimization of high-voltage GaN MOSC-HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 861-863.	0.8	0
13	Impact of annealing on ALD Al ₂ O ₃ gate dielectric for GaN MOS devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 907-910.	0.8	37
14	Over 1000V/30mA operation GaN-on-Si MOSFETs fabricated on Si substrates. Solid-State Electronics, 2011, 56, 73-78.	0.8	7
15	Modeling and experimental study of MOS channel mobility of etched GaN on silicon substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2433-2435.	0.8	2
16	Drift region optimization in high-voltage GaN MOS-gated HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2436-2438.	0.8	9
17	Channel scaling of hybrid GaN MOS-HEMTs. Solid-State Electronics, 2011, 56, 111-115.	0.8	24
18	Design and simulations of novel enhancementâ€“mode highâ€“voltage GaN vertical hybrid MOSâ€“HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1944-1948.	0.8	5

#	ARTICLE	IF	CITATIONS
19	Enhancement-mode GaN hybrid MOS-HEMTs with breakdown voltage of 1300V. Power Semiconductor Devices & IC's, 2009 ISPSD 2009 21st International Symposium on, 2009, , .	0.0	8
20	Comparative study of 4H-SiC and 2H-GaN MOS capacitors and FETs. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2478-2486.	0.8	10
21	Experimental Identification of Extra Type of Charges at SiO ₂ /SiC Interface in 4H-SiC. Materials Science Forum, 0, 645-648, 519-522.	0.3	2
22	Study of High Temperature Microwave Annealing on the Performance of 4H-SiC MOS Capacitors. Materials Science Forum, 0, 717-720, 769-772.	0.3	0